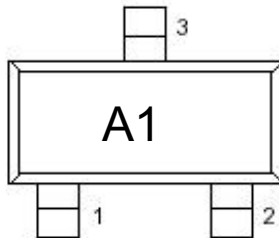


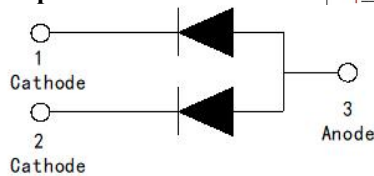
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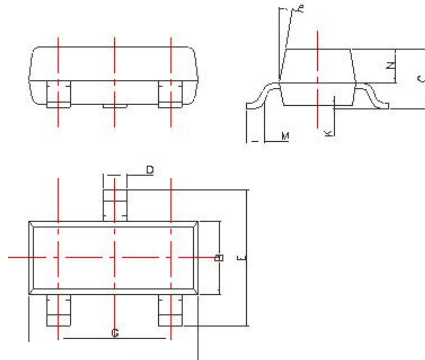
Marking: A1



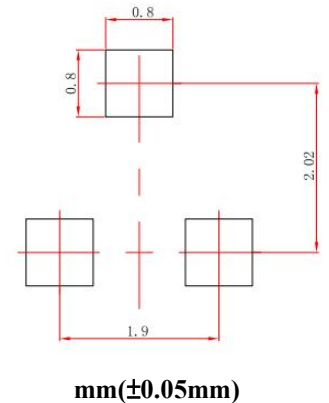
Top view



SOT-23 Dimension



DIM	Millimeters
A	2.85~3.04
B	1.30±0.10
C	1.00±0.10
D	0.45±0.05
E	2.25~2.55
G	1.90±0.1
K	0.00-0.10
M	0.20 min
N	0.60±0.10
P	7±2°

SOT-23
Suggested Layout

MAXIMUM RATINGS (Ta=25°C)

Characteristic	Symbol	Rating	Unit
Continuous Reverse Voltage	V_R	70	Vdc
Peak Forward Current	I_F	200	mAdc
Peak Forward Surge Current	$I_{FM(surge)}$	500	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board(1) TA=25°C	P_D	225	mW
Total Device Dissipation Alumina Substrate,(2) TA=25°C	P_D	300	mW
Junction and Storage Temperature	T_J , T_{stg}	150 , -55 ~150	°C

- FR-5=1.0×0.75×0.062in, printed-circuit board.
- Alumina=0.4×0.3×0.024in, 99.5%alumina

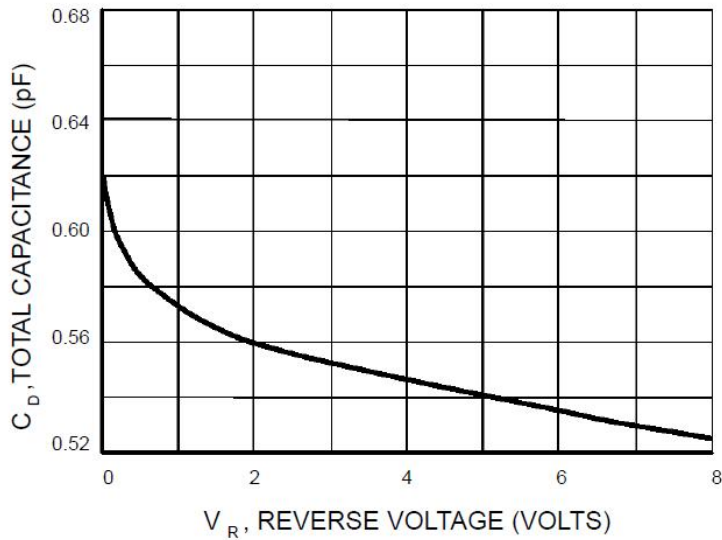
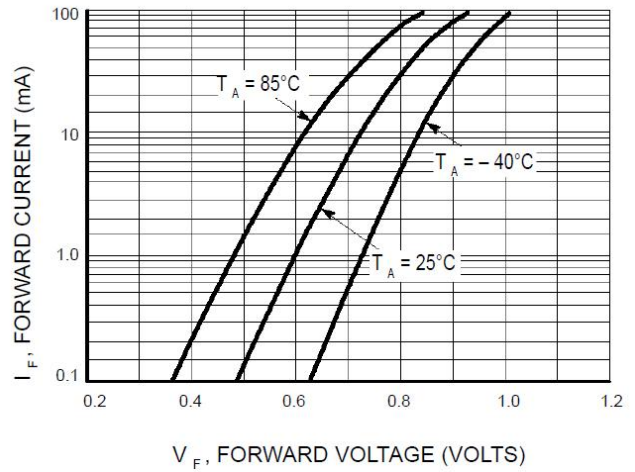
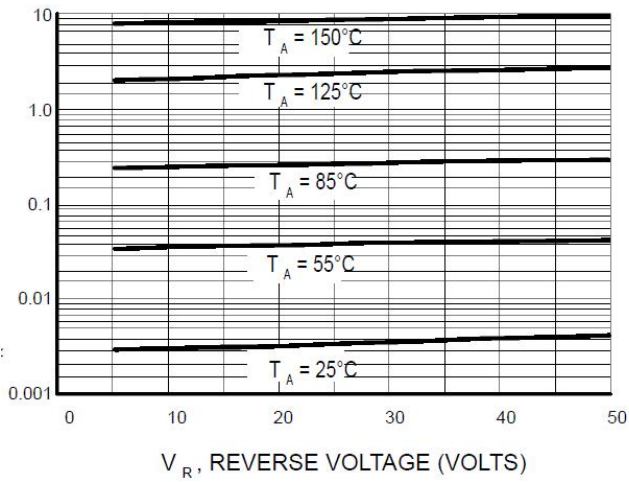
ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise noted)

Characteristic	Symbol	Test Condition	Min	Type	Max	Unit
Reverse Voltage Leakage Current	I_R	$V_R=70Vdc$	--	--	2.5	μA
		$V_R=70Vdc, T_j=150^\circ C$	--	--	50	
		$V_R=25Vdc, T_j=150^\circ C$	--	--	30	
Reverse Breakdown Voltage	$V_{(BR)}$	$I_{BR}=100 \mu A dc$	70	--	--	Vdc
Forward Voltage	V_F	$I_F=1mAdc$	--	--	715	mV
		$I_F=10mAdc$	--	--	855	
		$I_F=50mAdc$	--	--	1000	
		$I_F=150mAdc$	--	--	1250	
Diode Capacitance	C_D	$V_R=0, f=1.0MHz$	--	--	1.5	pF
Forward Recovery Voltage	V_{FR}	$I_F=10mAdc, t_r=20ns$	--	--	1.75	Vdc
Reverse Recovery Time	t_{rr}	$I_F=I_R=10mAdc,$ $R_L=100\Omega$	--	--	6.0	nS

CDD56-ME

DIODE

Typical Characteristics



Note: Specifications are subject to change without notice. For more detail and update, please visit our website.